

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

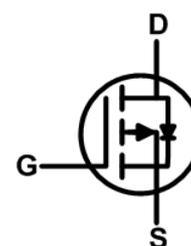
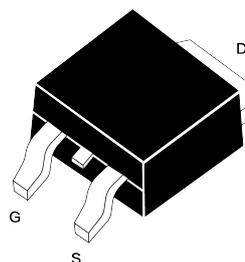
BVDSS	RDSON	ID
-20V	12mΩ	-40A

Description

The JH40P02 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The JH40P02 meet the RoHS and Gree Product requirement 100% EAS guaranteed with full function reliability approved.

TO-252 Pin Configuration



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	$T_A = 25^\circ\text{C}$	-40
		$T_A = 100^\circ\text{C}$	-15.7
Pulsed Drain Current ¹	I_{DM}	-66	A
Single Pulse Avalanche Energy ²	EAS	28.8	mJ
Total Power Dissipation	P_D	30	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	$R_{\theta JA}$	41.6	$^\circ\text{C}/\text{W}$

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V_{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20	-	-	V	
Gate-body Leakage current	I_{GSS}	V _{DS} = 0V, V _{GS} = ±12V	-	-	±100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} = -20V, V _{GS} = 0V	T _J = 25°C	-	-	-1	μA
			T _J = 100°C	-	-	-100	
Gate-Threshold Voltage	V_{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-0.65	-1	V	
Drain-Source On-Resistance ⁴	R_{DS(on)}	V _{GS} = -4.5V, I _D = -8A	-	12.0	18	mΩ	
		V _{GS} = -2.5V, I _D = -6A	-	17	23		
Forward Transconductance ⁴	g_{fs}	V _{DS} = -4.5V, I _D = -8A	-	36	-	S	
Dynamic Characteristics⁵							
Input Capacitance	C_{iss}	V _{DS} = -10V, V _{GS} = 0V, f = 1MHz	-	1630	-	pF	
Output Capacitance	C_{oss}		-	211	-		
Reverse Transfer Capacitance	C_{rss}		-	187	-		
Gate Resistance	R_g	f = 1MHz	-	10	-	Ω	
Switching Characteristics⁵							
Total Gate Charge	Q_g	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -8A	-	12	-	nC	
Gate-Source Charge	Q_{gs}		-	1.8	-		
Gate-Drain Charge	Q_{gd}		-	3.2	-		
Turn-On Delay Time	t_{d(on)}	V _{GS} = -4.5V, V _{DD} = -10V, R _G = 3Ω, I _D = -8A	-	17	-	ns	
Rise Time	t_r		-	25.5	-		
Turn-Off Delay Time	t_{d(off)}		-	32	-		
Fall Time	t_f		-	15	-		
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴	V_{SD}	I _S = -8A, V _{GS} = 0V	-	-	-1.2	V	
Continuous Source Current	I_S	T _A = 25°C	-	-	-40	A	

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C.
2. The EAS data shows Max. rating . The test condition is V_{DD} = -25V, V_{GS} = -10V, L = 0.1mH, I_{AS} = -24A
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test..

Typical Characteristics

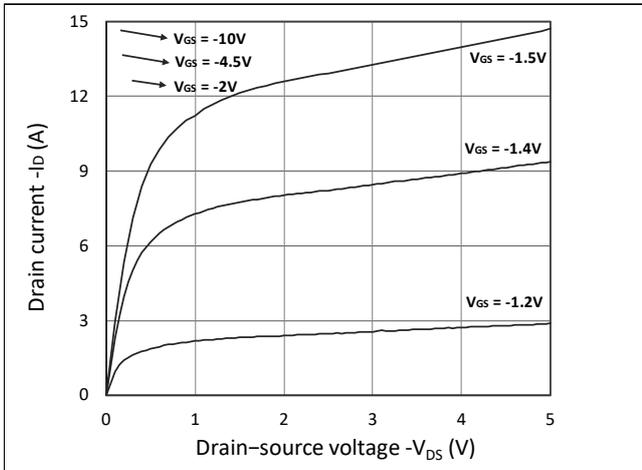


Figure 1. Output Characteristics

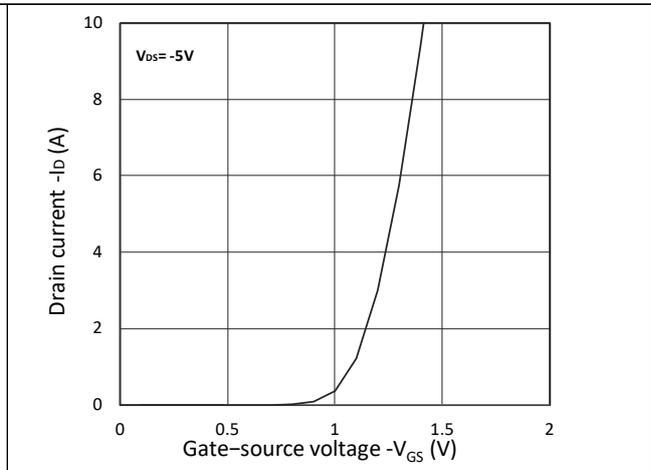


Figure 2. Transfer Characteristics

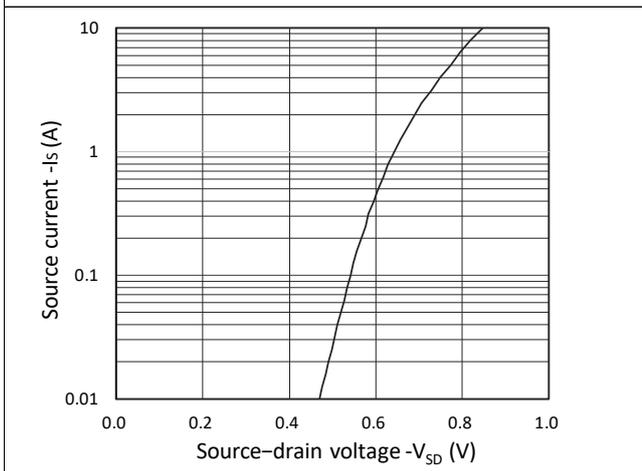


Figure 3. Forward Characteristics of Reverse

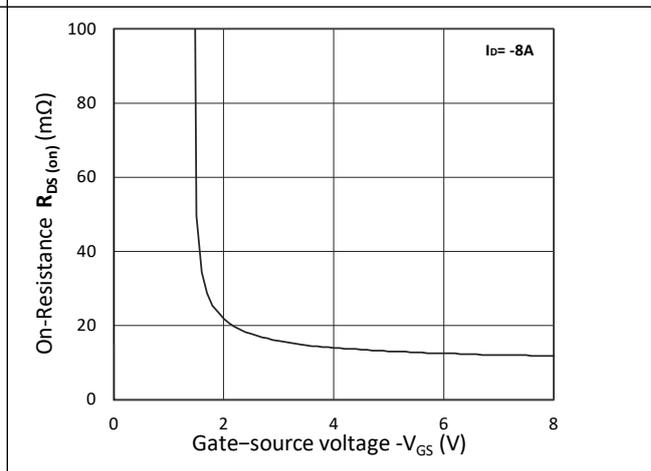


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

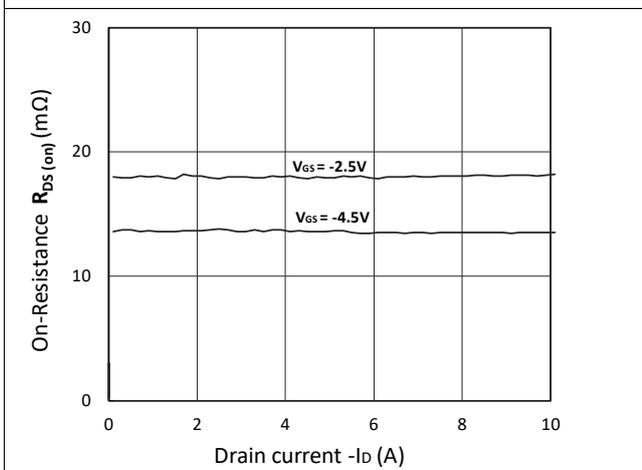


Figure 5. $R_{DS(ON)}$ vs. I_D

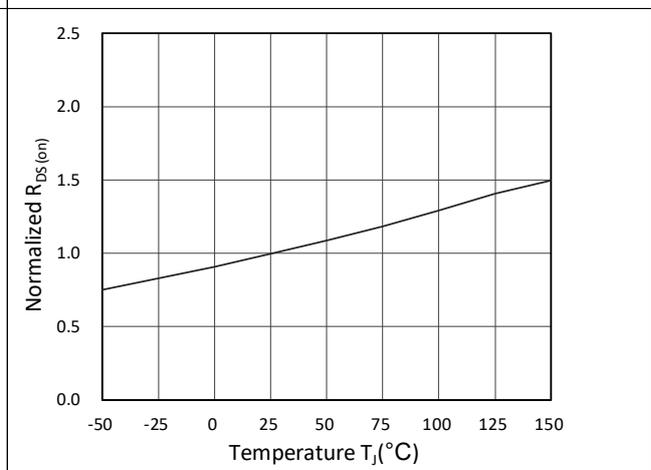


Figure 6. Normalized $R_{DS(ON)}$ vs. Temperature

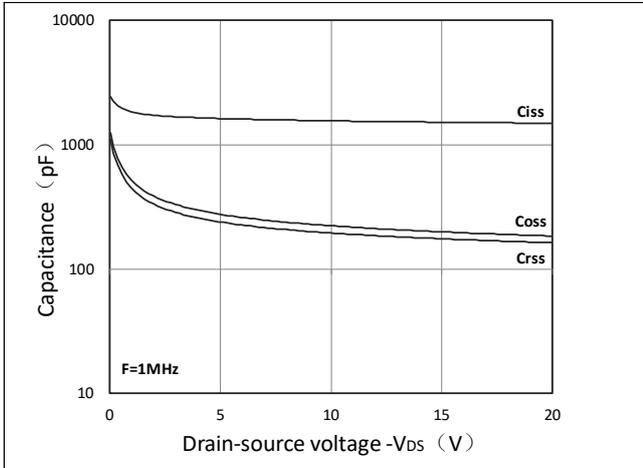


Figure 7. Capacitance Characteristics

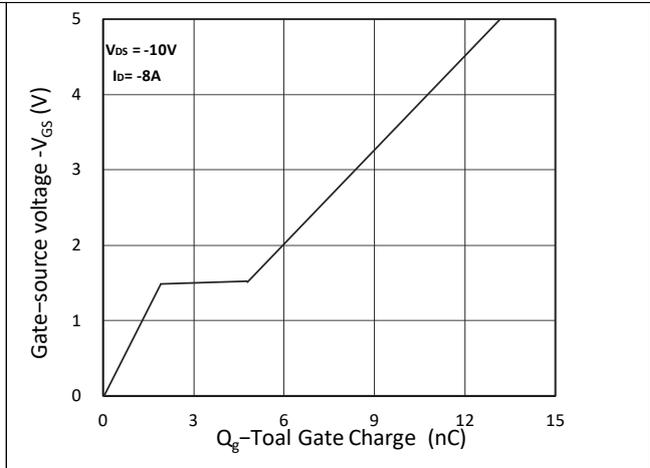


Figure 8. Gate Charge Characteristics

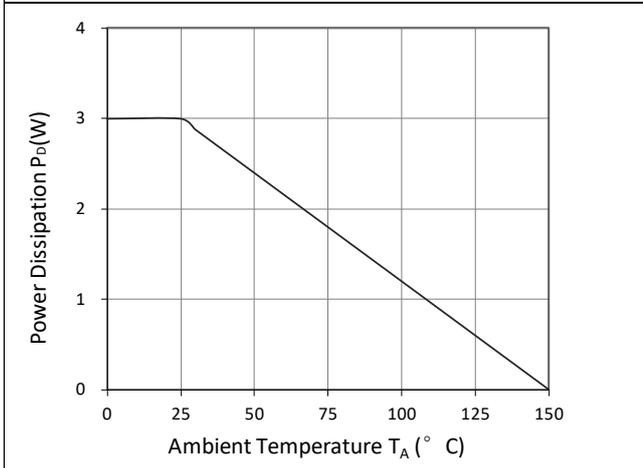


Figure 9. Power Dissipation

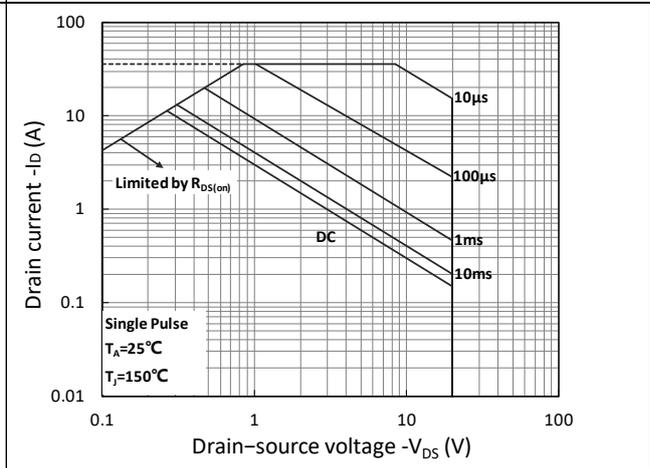


Figure 10. Safe Operating Area

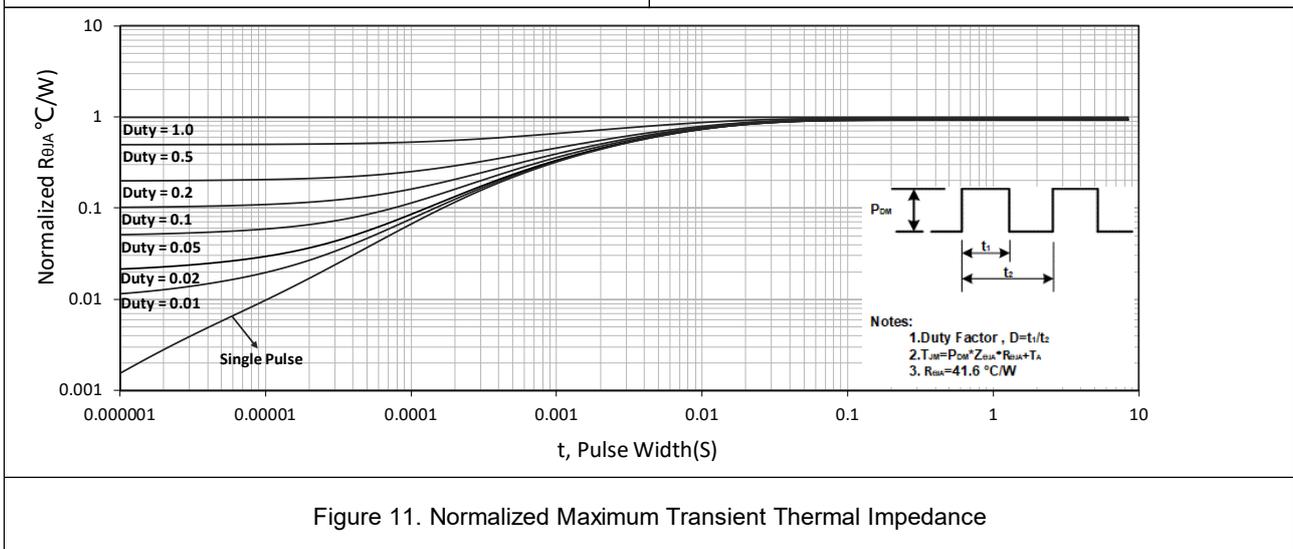
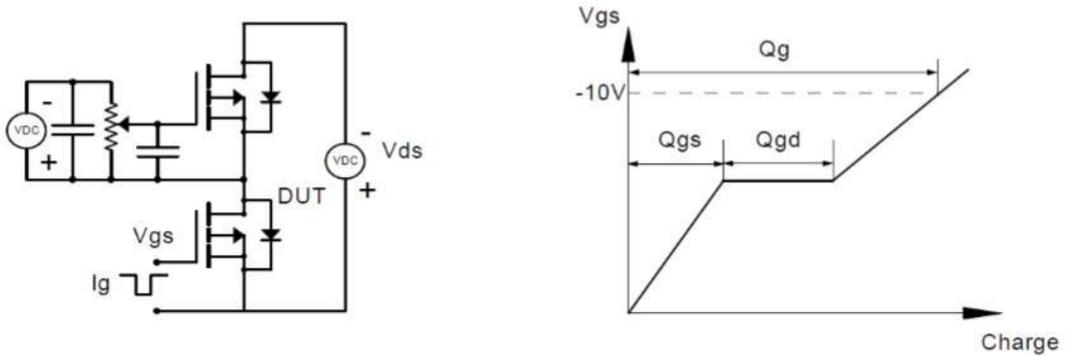


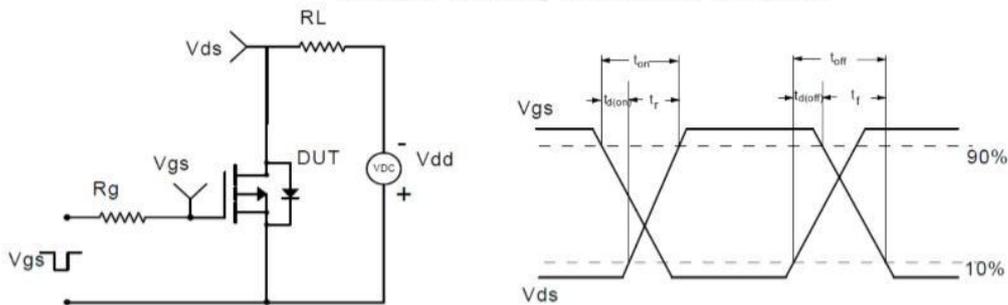
Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

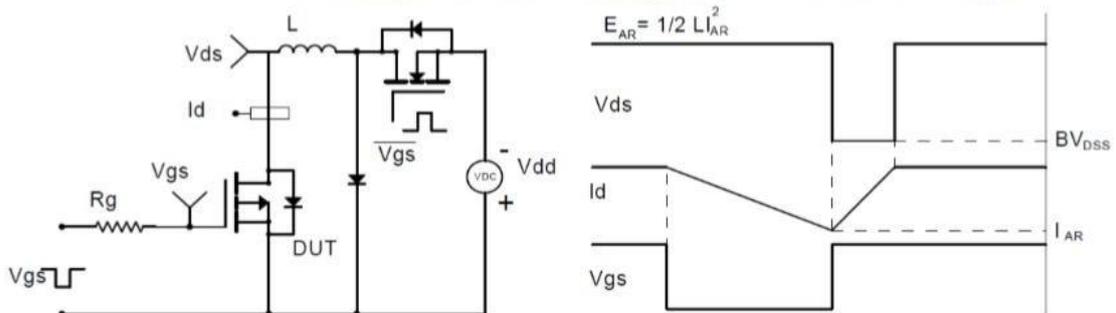
Gate Charge Test Circuit & Waveform



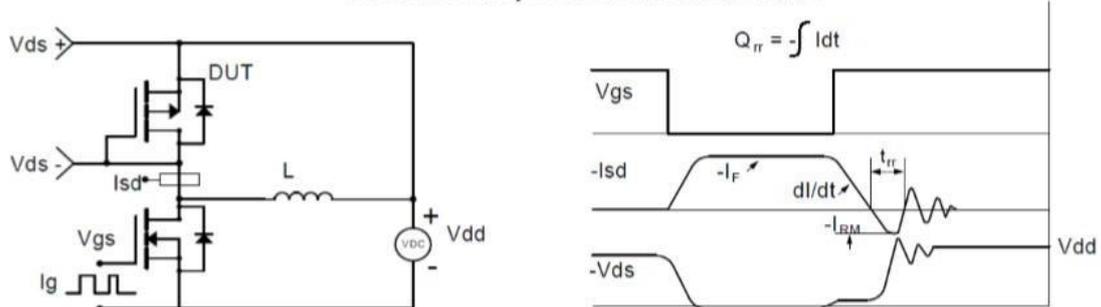
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

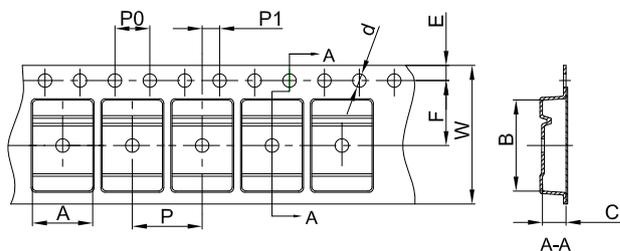


Diode Recovery Test Circuit & Waveforms



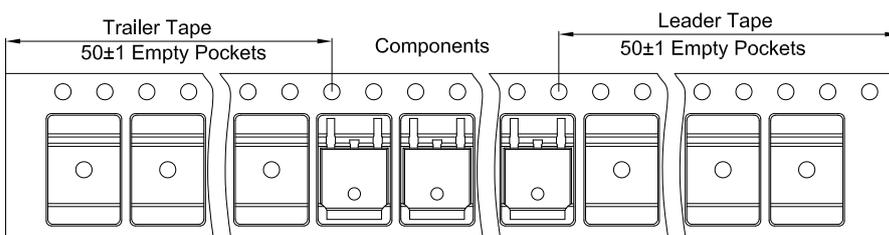
TO-252-2L Tape and Reel

TO-252 Embossed Carrier Tape

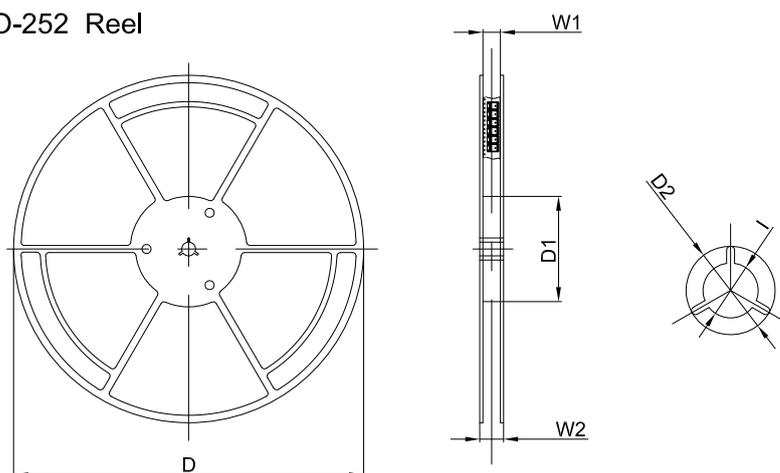


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00

TO-252 Tape Leader and Trailer

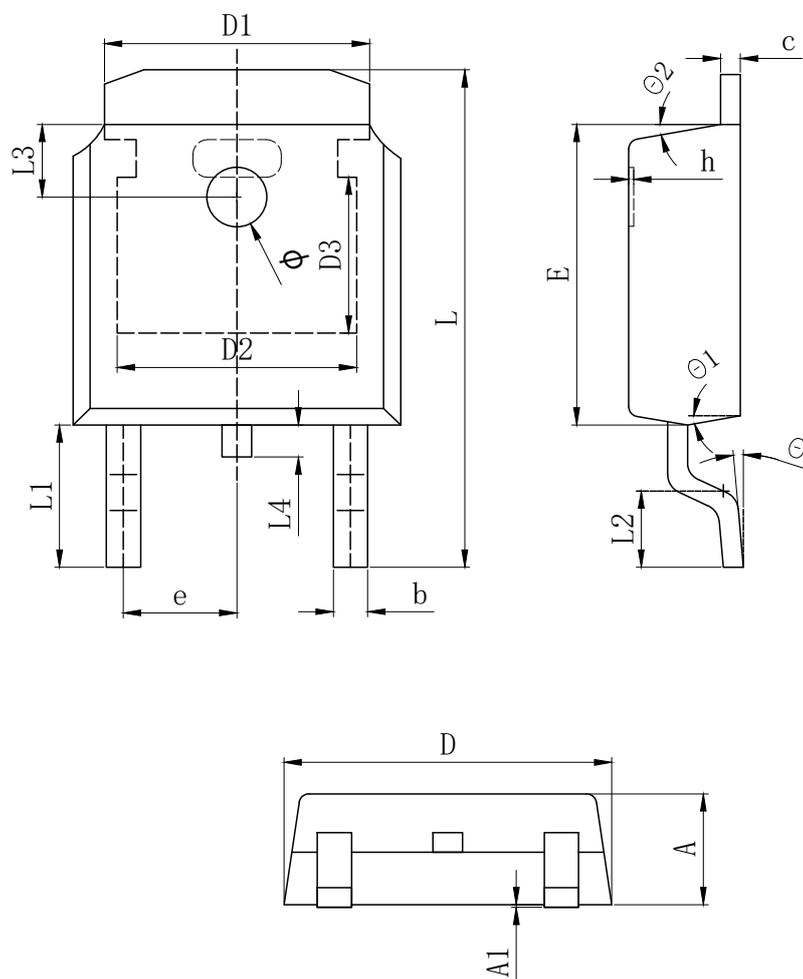


TO-252 Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	W1	W2	I
13" Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c (电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
ϕ	1.100	1.200	1.300
θ	0°		8°
θ_1	9° TYP		
θ_2	9° TYP		

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